DAP222M3T5G

Preferred Device

Product Preview Common Anode Silicon Dual Switching Diodes

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SOT–723 package which is designed for low power surface mount applications, where board space is at a premium.

- Fast t_{rr}
- Low C_D
- ESD Performance: Human Body Model; > 2000 V, Machine Model > 200 V
- Available in 4 mm Tape and Reel
- This is a Pb–Free Device

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Value	Unit	
Reverse Voltage	V _R	80	V	
Peak Reverse Voltage	V _{RM}	80	V	
Forward Current	١ _F	100	mA	
Peak Forward Current	I _{FM}	300	mA	
Peak Forward Surge Current	I _{FSM} (Note 1)	2.0	A	

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit	
Power Dissipation	PD	260	mW	
Junction Temperature	TJ	150	°C	
Storage Temperature	T _{stg}	-55 ~ +150	°C	

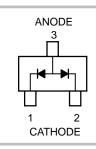
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

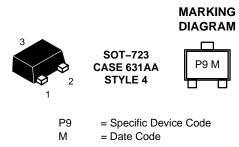
1. t = 1.0 μS.



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ORDERING INFORMATION

Device	Package	Shipping [†]	
DAP222M3T5G	SOT-723	8000/Tape & Reel	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

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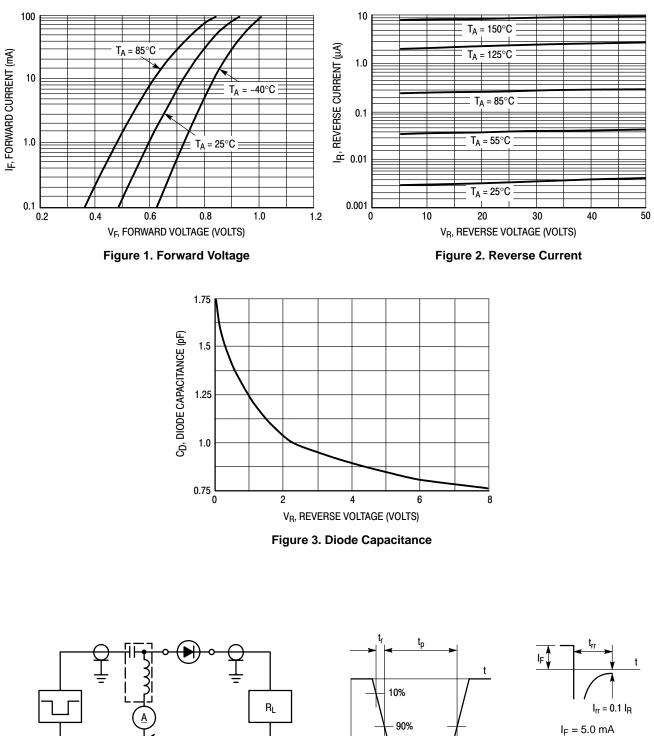
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	-	0.1	μΑ
Forward Voltage	V _F	I _F = 100 mA	-	1.2	V
Reverse Breakdown Voltage	V _R	I _R = 100 μA	80	_	V
Diode Capacitance	CD	V _R = 6.0 V, f = 1.0 MHz	-	3.5	pF
Reverse Recovery Time t _{rr} (Note		I_{F} = 5.0 mA, V_{R} = 6.0 V, R_{L} = 100 Ω,I_{rr} = 0.1 I_{R}	-	4.0	ns

2. t_{rr} Test Circuit for DAP222 in Figure 4.

DAP222M3T5G

TYPICAL ELECTRICAL CHARACTERISTICS



 $V_R = 6 V$ $R_L = 100 \Omega$

OUTPUT PULSE

RECOVERY TIME EQUIVALENT TEST CIRCUIT

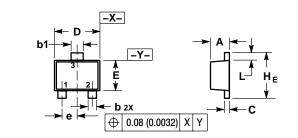


 V_{R}

 $t_p = 2 \ \mu s$ $t_r = 0.35 \ ns$ INPUT PULSE

PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE B



NOTES:

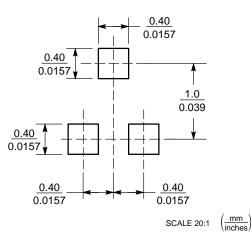
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.45	0.50	0.55	0.018	0.020	0.022	
b	0.15	0.21	0.27	0.0059	0.0083	0.0106	
b1	0.25	0.31	0.37	0.010	0.012	0.015	
С	0.07	0.12	0.17	0.0028	0.0047	0.0067	
D	1.15	1.20	1.25	0.045	0.047	0.049	
E	0.75	0.80	0.85	0.03	0.032	0.034	
е	0.40 BSC			0.016 BSC			
ΗE	1.15	1.20	1.25	0.045	0.047	0.049	
L	0.15	0.20	0.25	0.0059	0.0079	0.0098	

STYLE 4: PIN 1. CATHODE 2. CATHODE

3. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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